

## SW Test Workshop Semiconductor Wafer Test Workshop

## Improvement of High Speed Testing through Signal Path Enhancement





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## Introduction

- As IC technology advances, more components are integrated into a single chip to increase functionality and reduce cost of manufacturing
- Thus, effective and efficient wafer-level test systems are in demand to screen off failed chips before packaging to significantly decreases cost of manufacturing
- To test wafer precisely, at-speed test which conducts test at the actual operation speed (which is usually high)
- Thus, high performance probe cards are in demand, particularly at high speed

## **Problem Statement**

- We found that ordinary probe card consistently overkill particularly in some high speed test (eg. Mbist high speed, Core high speed test etc)
- We required high performance probe card for high performance ICs testing which required
  - ✓ High pin count
  - ✓ High operating frequency
  - ✓ Good power distribution network
  - ✓ Low crosstalk noise between needles

## **Knowing Probe Card Critical Design Parameters**

#### **Design A**



- Probe fan-out on 4 sides to better improve probe clearance.
- Identify critical signals and shielding it for cleaner electrical results.
- High grade epoxy with improve insulation properties.

#### **Design B**



 Probe clearance reduce on 2 sides (diagonal side).
 Critical signals not shielded
 Low grade epoxy

## **Knowing Probe Card Critical Design Parameters**





What is happening at signal critical phase.

# Extending GND shield on critical signals

Schematic

# Understanding Signal Path (TDR- Important Conditions)



# Understanding Signal Path (TDR- Important Conditions)



Extending GND shield on Aggressor or Victim signal path lines.

Design



## **Yield Summary Comparison**

Probe card from Design A specially designed for high speed testing shows better performance:

- Better Mbist High Speed test by 5-8%
- Better Core Speed test by 8-20%

	Split			F Yield Loss		Pass		
WF	P/C vendor	Cleaning frequency	Cleaning OD	MBIST_Low_Speed	MBIST_High_Speed	Bin1_1.5Ghz	Bin1_1.4Ghz	
v	Design B	5 times	40um	3.0	5.6	74.1	8.8	
v	Design A	5 times	40um	3.0	0.5	86.5	1.0	- <b>1</b>
w	Design B	5 times	40um	5.7	3.3	73.6	6.9	25.64
w	Design A	5 times	40um	5.6	0.3	82.0	1.5	
X	Design B	5 times	40um	5.0	7.4	69.5	10.5	
x	Design A	5 times	40um	5.0	0.4	85.2	1.2	
Y	Design B	5 times	40um	3.1	4.2	78.3	5.5	
Y	Design A	5 times	40um	3.1	0.4	84.7	2.2	
Ζ	Design B	5 times	40um	7.9	9.5	45.2	24.9	
Z	Design A	5 times	40um	8.0	0.7	72.9	4.3	
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## **Probe Cards Characterization and Comparison**

All IDDs are well correlated for both probe cards

IDD\_VDD\_CPU



## **Probe Cards Characterization and Comparison**

 Specially designed Probe card from Feinmetall having lower Vmin by 10mV in Core Speed Test





## **Probe Cards Characterization and Comparison**

### **Design A**

### **Design B**





Smooth and clean output

- Crosstalk noises
- Causes unstable output

## Conclusion

- This presentation summarized our works to achieve high performance probe card for high speed testing
- Special designed probe card with better fan-out and shielding of critical pins out perform ordinary probe card in high speed testing
- Lower Vmin and better noise isolation achieved

## **Thank You**